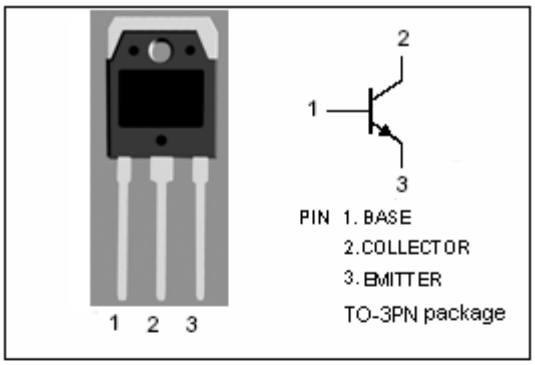
isc Silicon NPN Power Transistor 2SC4060

DESCRIPTION

- High Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$= 450V(Min)
- High Switching Speed
- High Reliability



APPLICATIONS

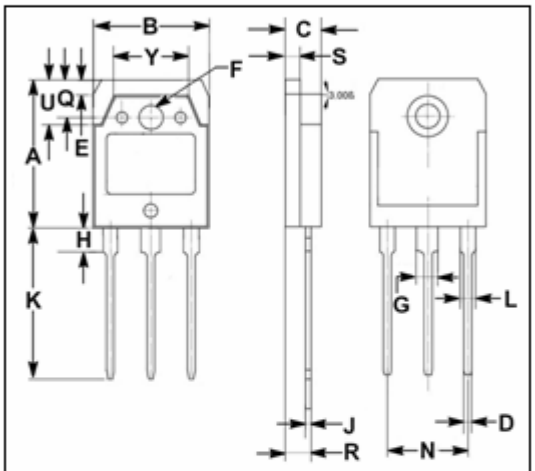
- Designed for switching regulator and general purpose applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	600	V
V_{CEO}	Collector-Emitter Voltage	450	V
V_{EBO}	Emitter-Base voltage	7	V
I_C	Collector Current-Continuous	20	A
I_{CM}	Collector Current-Peak	40	A
I_B	Base Current-Continuous	7	A
I_{BM}	Base Current-Peak	14	A
P_C	Collector Power Dissipation @ T_C=25℃	150	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	0.83	℃/W



DIM	mm MIN	MAX
A	19.60	20.10
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	20.00	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.10
Y	9.90	10.10

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 30mA; I_B= 0	450			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 10A; I_B= 2A			1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 10A; I_B= 2A			1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 600V; I_E= 0			0.1	mA
I_{CEO}	Collector Cutoff Current	V_{CE}= 450V; I_B= 0			0.1	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 7V; I_C= 0			0.1	mA
h_{FE-1}	DC Current Gain	I_C= 10A; V_{CE}= 5V	10			
h_{FE-2}	DC Current Gain	I_C= 1mA; V_{CE}= 5V	5			
f_T	Current-Gain—Bandwidth Product	I_C= 2A; V_{CE}= 10V		20		MHz

Switching Times

t_{on}	Turn-on Time	I_C= 10A,I_{B1}= 2A; I_{B2}= -4A R_L= 15Ω; V_{BB2}= 4V			0.5	μs
t_{stg}	Storage Time				2.0	μs
t_f	Fall Time				0.2	μs